

ABSTRACT

TUNGSTEN SINTERED SPUTTERING TARGET

5 Provided is a tungsten sintered sputtering target, wherein the phosphorus content is 1wtppm or less and the remainder is other unavoidable impurities and tungsten. The inclusion of phosphorus heavily affects the abnormal grain growth of tungsten and the deterioration in the target strength. In particular, if phosphorus is contained in an amount exceeding 1ppm, crystal grains subject to abnormal grain growth will exist in the tungsten target. Thus, the object is to prevent the abnormal grain growth of tungsten and improve the product yield of the target by strongly recognizing the phosphorus contained in the tungsten as a harmful
.0 impurity and controlling the inclusion thereof to be as low as possible.